DDR3 SDRAM

MT41J512M4 – 64 Meg x 4 x 8 Banks
MT41J256M8 – 32 Meg x 8 x 8 Banks
MT41J128M16 – 16 Meg x 16 x 8 Banks

Features

- $V_{DD} = V_{DDQ} = 1.5V \pm 0.075V$
- 1.5V center-terminated push/pull I/O
- Differential bidirectional data strobe
- 8*n*-bit prefetch architecture
- Differential clock inputs (CK, CK#)
- 8 internal banks
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Programmable CAS READ latency (CL)
- Posted CAS additive latency (AL)
- Programmable CAS WRITE latency (CWL) based on ^{t}CK
- Fixed burst length (BL) of 8 and burst chop (BC) of 4 (via the mode register set [MRS])
- Selectable BC4 or BL8 on-the-fly (OTF)
- Self refresh mode
- T_C of 0°C to 95°C
  - 64ms, 8192 cycle refresh at 0°C to 85°C
  - 32ms, 8192 cycle refresh at 85°C to 95°C
- Self refresh temperature (SRT)
- Write leveling
- Multipurpose register
- Output driver calibration

Options[1] / Marking

• Configuration	
– 512 Meg x 4	512M4
– 256 Meg x 8	256M8
– 128 Meg x 16	128M16
• FBGA package (Pb-free) – x4, x8	
– 78-ball (8mm x 10.5mm) Rev. H,M,J,K	DA
– 78-ball (9mm x 11.5mm) Rev. D	HX
• FBGA package (Pb-free) – x16	
– 96-ball (9mm x 14mm) Rev. D	HA
– 96-ball (8mm x 14mm) Rev. K	JT
• Timing – cycle time	
– 938ps @ CL = 14 (DDR3-2133)	-093
– 1.071ns @ CL = 13 (DDR3-1866)	-107
– 1.25ns @ CL = 11 (DDR3-1600)	-125
– 1.5ns @ CL = 9 (DDR3-1333)	-15E
– 1.87ns @ CL = 7 (DDR3-1066)	-187E
• Operating temperature	
– Commercial (0°C ≤ T_C ≤ +95°C)	None
– Industrial (–40°C ≤ T_C ≤ +95°C)	IT
• Revision	:D/:H/:J/:K/:M

Note: 1. Not all options listed can be combined to define an offered product. Use the part catalog search on http://www.micron.com for available offerings.

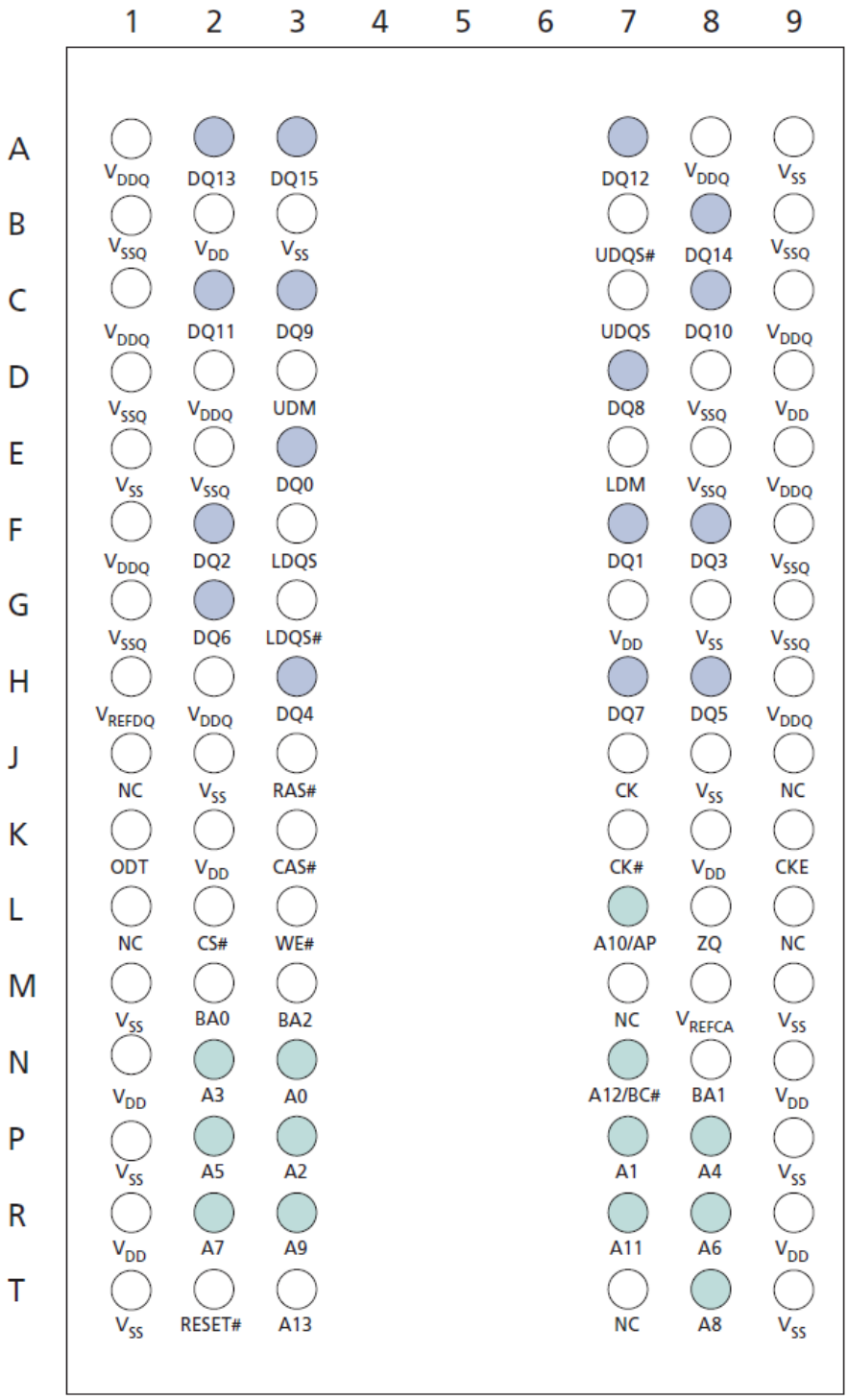
Table 1: Key Timing Parameters

Speed Grade	Data Rate (MT/s)	Target ^{t}RCD-^{t}RP-CL	^{t}RCD (ns)	^{t}RP (ns)	CL (ns)
-093[1, 2, 3, 4]	2133	14-14-14	13.09	13.09	13.09
-107[1, 2, 3]	1866	13-13-13	13.91	13.91	13.91
-125[1, 2,]	1600	11-11-11	13.75	13.75	13.75
-15E[1,]	1333	9-9-9	13.5	13.5	13.5
-187E	1066	7-7-7	13.1	13.1	13.1

Contents

Ball Assignments and Descriptions

Figure 7: 96-Ball FBGA – x16 (Top View)



Note: 1. Ball descriptions listed in Table 4 (page 20).

Table 4: 96-Ball FBGA – x16 Ball Descriptions

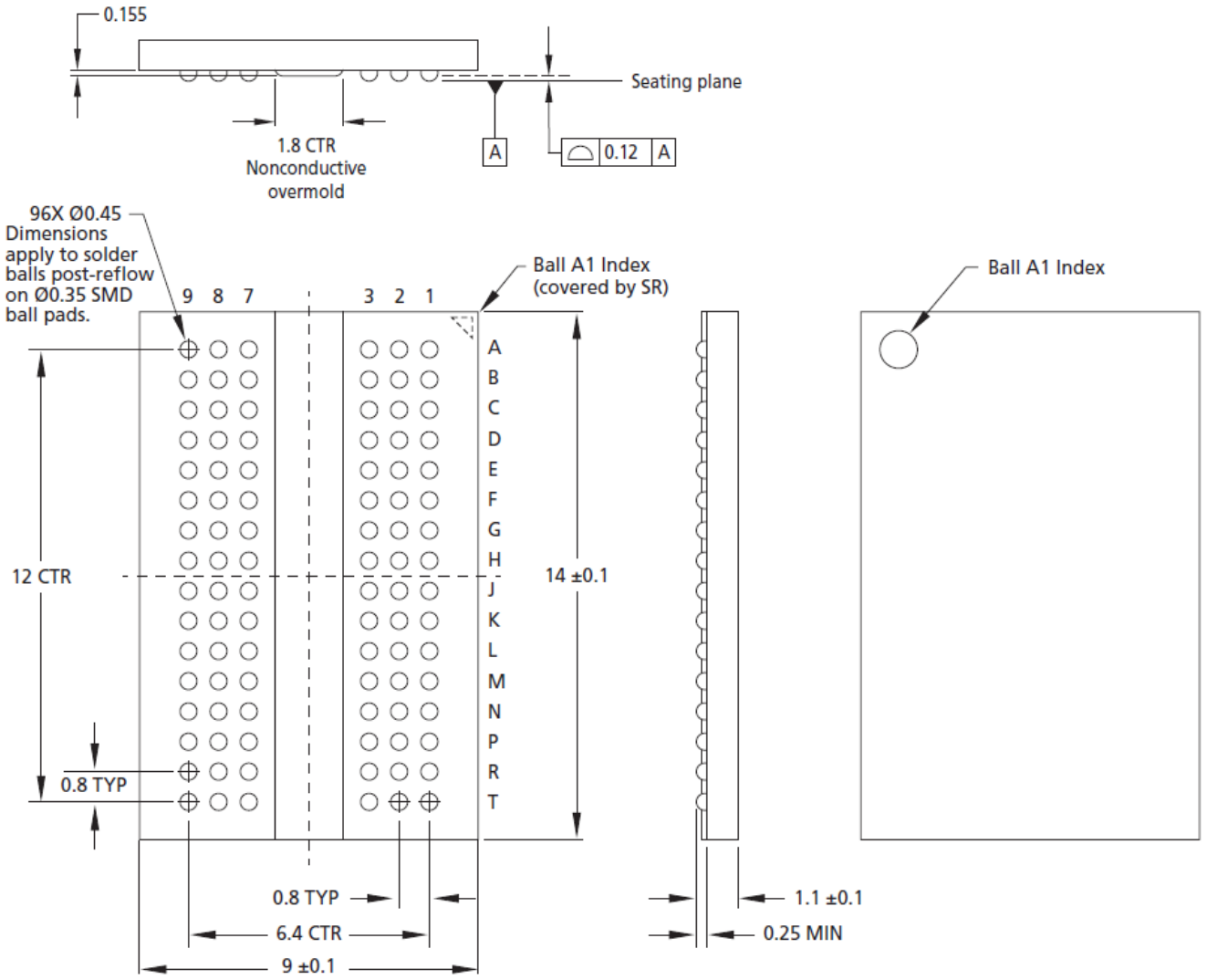
Symbol	Type	Description
A13, A12/BC#, A11, A10/AP, A[9:0]	Input	**Address inputs:** Provide the row address for ACTIVATE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one bank (A10 LOW, bank selected by BA[2:0]) or all banks (A10 HIGH). The address inputs also provide the op-code during a LOAD MODE command. Address inputs are referenced to V_{REFCA}. A12/BC#: When enabled in the mode register (MR), A12 is sampled during READ and WRITE commands to determine whether burst chop (on-the-fly) will be performed (HIGH = BL8 or no burst chop, LOW = BC4). See Table 65 (page 108).
BA[2:0]	Input	**Bank address inputs:** BA[2:0] define the bank to which an ACTIVATE, READ, WRITE, or PRECHARGE command is being applied. BA[2:0] define which mode register (MR0, MR1, MR2, or MR3) is loaded during the LOAD MODE command. BA[2:0] are referenced to V_{REFCA}.
CK, CK#	Input	**Clock:** CK and CK# are differential clock inputs. All control and address input signals are sampled on the crossing of the positive edge of CK and the negative edge of CK#. Output data strobe (DQS, DQS#) is referenced to the crossings of CK and CK#.
CKE	Input	**Clock enable:** CKE enables (registered HIGH) and disables (registered LOW) internal circuitry and clocks on the DRAM. The specific circuitry that is enabled/disabled is dependent upon the DDR3 SDRAM configuration and operating mode. Taking CKE LOW provides PRECHARGE POWER-DOWN and SELF REFRESH operations (all banks idle),or active power-down (row active in any bank). CKE is synchronous for power-down entry and exit and for self refresh entry. CKE is asynchronous for self refresh exit. Input buffers (excluding CK, CK#, CKE, RESET#, and ODT) are disabled during POWER-DOWN. Input buffers (excluding CKE and RESET#) are disabled during SELF REFRESH. CKE is referenced to V_{REFCA}.
CS#	Input	**Chip select:** CS# enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when CS# is registered HIGH. CS# provides for external rank selection on systems with multiple ranks. CS# is considered part of the command code. CS# is referenced to V_{REFCA}.
LDM	Input	**Input data mask:** LDM is a lower-byte, input mask signal for write data. Lower-byte input data is masked when LDM is sampled HIGH along with the input data during a write access. Although the LDM ball is input-only, the LDM loading is designed to match that of the DQ and DQS balls. LDM is referenced to V_{REFDQ}.
ODT	Input	**On-die termination:** ODT enables (registered HIGH) and disables (registered LOW) termination resistance internal to the DDR3 SDRAM. When enabled in normal operation, ODT is only applied to each of the following balls: DQ[15:0], LDQS, LDQS#, UDQS, UDQS#, LDM, and UDM. The ODT input is ignored if disabled via the LOAD MODE command. ODT is referenced to V_{REFCA}.
RAS#, CAS#, WE#	Input	**Command inputs:** RAS#, CAS#, and WE# (along with CS#) define the command being entered and are referenced to V_{REFCA}.
RESET#	Input	**Reset:** RESET# is an active LOW CMOS input referenced to V_{SS}. The RESET# input receiver is a CMOS input defined as a rail-to-rail signal with DC HIGH ≥ 0.8 × V_{DD} and DC LOW ≤ 0.2 × V_{DDQ}. RESET# assertion and de-assertion are asynchronous.

Table 4: 96-Ball FBGA – x16 Ball Descriptions (Continued)

Symbol	Type	Description
UDM	Input	**Input data mask:** UDM is an upper-byte, input mask signal for write data. Upper-byte input data is masked when UDM is sampled HIGH along with that input data during a WRITE access. Although the UDM ball is input-only, the UDM loading is designed to match that of the DQ and DQS balls. UDM is referenced to V_{REFDQ}.
DQ[7:0]	I/O	**Data input/output:** Lower byte of bidirectional data bus for the x16 configuration. DQ[7:0] are referenced to V_{REFDQ}.
DQ[15:8]	I/O	**Data input/output:** Upper byte of bidirectional data bus for the x16 configuration. DQ[15:8] are referenced to V_{REFDQ}.
LDQS, LDQS#	I/O	**Lower byte data strobe:** Output with read data. Edge-aligned with read data. Input with write data. Center-aligned to write data.
UDQS, UDQS#	I/O	**Upper byte data strobe:** Output with read data. Edge-aligned with read data. Input with write data. DQS is center-aligned to write data.
V_{DD}	Supply	**Power supply:** 1.5V ±0.075V.
V_{DDQ}	Supply	**DQ power supply:** 1.5V ±0.075V. Isolated on the device for improved noise immunity.
V_{REFCA}	Supply	**Reference voltage for control, command, and address:** V_{REFCA} must be maintained at all times (including self refresh) for proper device operation.
V_{REFDQ}	Supply	**Reference voltage for data:** V_{REFDQ} must be maintained at all times (excluding self refresh) for proper device operation.
V_{SS}	Supply	Ground.
V_{SSQ}	Supply	**DQ ground:** Isolated on the device for improved noise immunity.
ZQ	Reference	**External reference ball for output drive calibration:** This ball is tied to external 240Ω resistor RZQ, which is tied to V_{SSQ}.
NC	–	**No connect:** These balls should be left unconnected (the ball has no connection to the DRAM or to other balls).

Package Dimensions

Figure 10: 96-Ball FBGA – x16 (HA)



Note: 1. All dimensions are in millimeters.

Electrical Specifications – DC and AC

DC Operating Conditions

Table 23: DC Electrical Characteristics and Operating Conditions

All voltages are referenced to V_{SS}

Parameter/Condition	Symbol	Min	Nom	Max	Unit	Notes
Supply voltage	V_{DD}	1.425	1.5	1.575	V	1, 2
I/O supply voltage	V_{DDQ}	1.425	1.5	1.575	V	1, 2
Input leakage current Any input 0V ≤ V_{IN} ≤ V_{DD}, V_{REF} pin 0V ≤ V_{IN} ≤ 1.1V (All other pins not under test = 0V)	I_I	–2	–	2	µA	
V_{REF} supply leakage current V_{REFDQ} = V_{DD}/2 or V_{REFCA} = V_{DD}/2 (All other pins not under test = 0V)	I_{VREF}	–1	–	1	µA	4

Notes:
1. V_{DD} and V_{DDQ} must track one another. V_{DDQ} must be ≤ V_{DD}. V_{SS} = V_{SSQ}.
2. V_{DD} and V_{DDQ} may include AC noise of ±50mV (250 kHz to 20 MHz) in addition to the DC (0 Hz to 250 kHz) specifications. V_{DD} and V_{DDQ} must be at same level for valid AC timing parameters.
3. V_{REF} (see Table 24).
4. The minimum limit requirement is for testing purposes. The leakage current on the V_{REF} pin should be minimal.

Input Operating Conditions

Table 24: DC Electrical Characteristics and Input Conditions

All voltages are referenced to V_{SS}

Parameter/Condition	Symbol	Min	Nom	Max	Unit	Notes
V_{IN} low; DC/commands/address busses	V_{IL}	V_{SS}	n/a	See Table 25	V	
V_{IN} high; DC/commands/address busses	V_{IH}	See Table 25	n/a	V_{DD}	V	
Input reference voltage command/address bus	$V_{REFCA(DC)}$	0.49 × V_{DD}	0.5 × V_{DD}	0.51 × V_{DD}	V	1, 2
I/O reference voltage DQ bus	$V_{REFDQ(DC)}$	0.49 × V_{DD}	0.5 × V_{DD}	0.51 × V_{DD}	V	2, 3
I/O reference voltage DQ bus in SELF REFRESH	$V_{REFDQ(SR)}$	V_{SS}	0.5 × V_{DD}	V_{DD}	V	4
Command/address termination voltage (system level, not direct DRAM input)	V_{TT}	–	0.5 × V_{DDQ}	–	V	5

Notes:
1. $V_{REFCA(DC)}$ is expected to be approximately 0.5 × V_{DD} and to track variations in the DC level. Externally generated peak noise (noncommon mode) on V_{REFCA} may not exceed ±1% × V_{DD} around the $V_{REFCA(DC)}$ value. Peak-to-peak AC noise on V_{REFCA} should not exceed ±2% of $V_{REFCA(DC)}$.
2. DC values are determined to be less than 20 MHz in frequency. DRAM must meet specifications if the DRAM induces additional AC noise greater than 20 MHz in frequency.
3. $V_{REFDQ(DC)}$ is expected to be approximately 0.5 × V_{DD} and to track variations in the DC level. Externally generated peak noise (noncommon mode) on V_{REFDQ} may not exceed ±1% × V_{DD} around the $V_{REFDQ(DC)}$ value. Peak-to-peak AC noise on V_{REFDQ} should not exceed ±2% of $V_{REFDQ(DC)}$.
4. $V_{REFDQ(DC)}$ may transition to $V_{REFDQ(SR)}$ and back to $V_{REFDQ(DC)}$ when in SELF REFRESH, within restrictions outlined in the SELF REFRESH section.
5. V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors. Minimum and maximum values are system-dependent.

Electrical Characteristics – IDD Specifications

I/0 Current (VDDQ)
Peak dynamic current = 650 mA (during READ op.)
Steady current = 107 mA

Bandwidth requirement: DC - 40 MHz

Core Current (VDD)
Average current (steady): I_{DD0}
$I_{DD4} = I_{DD4R}$ during READ operation
$I_{DD4} = I_{DD4W}$ during WRITE operation

Bandwidth requirement: DC - 30 MHz

Table 22: I_{DD} Maximum Limits – Die Rev K

Speed Bin								
I_{DD}	Width	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	DDR3-2133	Unit	Notes
I_{DD0}	x4, x8	39	41	42	43	46	mA	1, 2
	x16	46	48	49	51	55	mA	
I_{DD1}	x4	46	50	52	55	57	mA	1, 2
	x8	50	54	56	58	60	mA	
	x16	62	67	69	72	75	mA	

Table 22: I_{DD} Maximum Limits – Die Rev K (Continued)

Speed Bin								
I_{DD}	Width	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	DDR3-2133	Unit	Notes
I_{DD2P0} (Slow)	All	12	12	12	12	12	mA	1, 2
I_{DD2P1} (Fast)	All	15	15	15	15	15	mA	1, 2
I_{DD2Q}	All	22	22	22	22	22	mA	1, 2
I_{DD2N}	All	23	23	23	23	23	mA	1, 2
I_{DD2NT}	x4,x8	29	32	34	36	40	mA	1, 2
	x16	33	36	37	39	43	mA	
I_{DD3P}	All	22	22	22	22	22	mA	1, 2
I_{DD3N}	x4,x8	31	33	35	37	40	mA	1, 2
	x16	33	36	37	39	43	mA	
I_{DD4R}	x4	70	84	96	106	120	mA	1, 2
	x8	74	88	100	110	125	mA	
	x16	95	115	135	155	180	mA	
I_{DD4W}	x4	75	87	99	110	122	mA	1, 2
	x8	79	91	103	114	126	mA	
	x16	107	127	146	164	184	mA	
I_{DD5B}	All	109	111	112	114	120	mA	1, 2
I_{DD6}	All	12	12	12	12	12	mA	1, 2, 3
I_{DD6ET}	All	15	15	15	15	15	mA	2, 4
I_{DD7}	x4, x8	128	157	163	171	190	mA	1, 2
	x16	159	179	202	226	248	mA	
I_{DD8}	All	I_{DD2P0} + 2mA	I_{DD2P0} + 2mA	I_{DD2P0} + 2mA	I_{DD2P0} + 2mA	I_{DD2P0} + 2mA	mA	1, 2